**Product data sheet** 

#### **Product profile** 1.

## 1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT186A (TO-220F) plastic package.

## 1.2 Features and benefits

- Fast switching
- High voltage capability

- Isolated package
- Low thermal resistance

# 1.3 Applications

- DC-to-DC converters
- High-frequency electronic lighting ballast applications
- Inverters
- Motor control systems

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{\mathbb{C}}$	collector current	see Figure 1; see Figure 2; see Figure 4	-	-	4	Α
P <sub>tot</sub>	total power dissipation	$T_h \le 25  \text{C}$ ; see Figure 3	-	-	26	W
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	1050	V
Static chara	acteristics					
h <sub>FE</sub>	DC current gain	$I_C = 0.1 \text{ A}$ ; $V_{CE} = 5 \text{ V}$ ; $T_h = 25 \text{ C}$ ; see Figure 11	48	66	100	
		$I_C = 0.8 \text{ A}; V_{CE} = 3 \text{ V}; T_h = 25 \text{ C};$ see Figure 12	25	42	50	



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector	mb	C I
3	Е	emitter		В
mb	n.c.	isolated		E sym123
			SOT186A (TO-220	PF)

# 3. Ordering information

Table 3. Ordering information

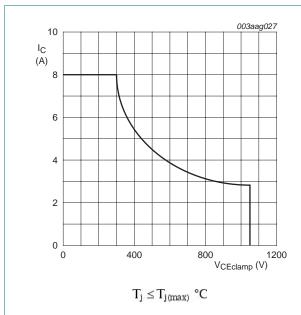
Type number	Package		
	Name	Description	Version
BUJ302AX	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0 V$	-	1050	V
$V_{CEO}$	collector-emitter voltage	I <sub>B</sub> = 0 A	-	400	V
I <sub>C</sub>	collector current	see Figure 1; see Figure 2; see Figure 4	-	4	Α
I <sub>CM</sub>	peak collector current		-	8	Α
I <sub>B</sub>	base current	DC	-	2	Α
I <sub>BM</sub>	peak base current		-	4	Α
P <sub>tot</sub>	total power dissipation	T <sub>h</sub> ≤ 25 °C; see <u>Figure 3</u>	-	26	W
$T_{stg}$	storage temperature		-65	150	$\mathcal C$
T <sub>j</sub>	junction temperature		-	150	${\mathcal C}$
$V_{EBO}$	emitter-base voltage	$I_C = 0 \text{ A}; I_E = 2 \text{ A}; t_p < 10 \text{ ms}$	-	24	V



$$\begin{split} V_{\mathit{CL(CE)}} \leq 1000 \; V; V_{\mathit{CC}} = 150 \; V; V_{\mathit{BB}} = \, -5 \; V; \\ L_{\mathit{B}} = 1 \, \mu H; L_{\mathit{C}} = 200 \, \mu H \end{split}$$

Fig 1. Reverse bias safe operating area

Fig 2. Test circuit for reverse bias safe operating area

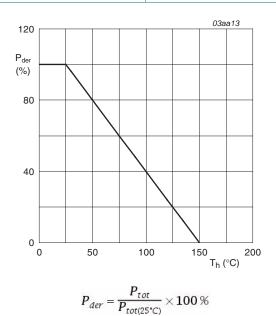
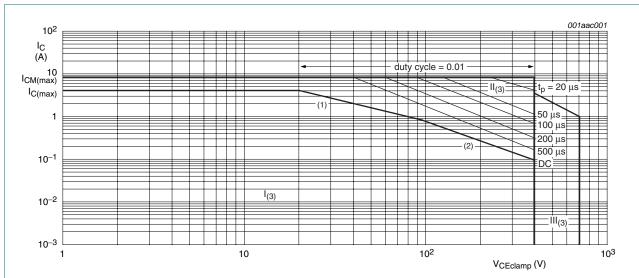


Fig 3. Normalized total power dissipation as a function of heatsink temperature



- 1)Ptot maximum and Ptot peak maximum lines
- 2)Second breakdown limits
- 3) I = Region of permissable DC operation
  - II = Extension for repetitive pulse operation
  - III = Extension during turn-on in single transistor converters provided that RBE  $\leq$  100  $\Omega$  and tp  $\leq$  0.6  $\mu$ s

Forward bias safe operating area for Tmb ≤ 25 ℃ Fig 4.

# 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 5	-	-	4.8	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W

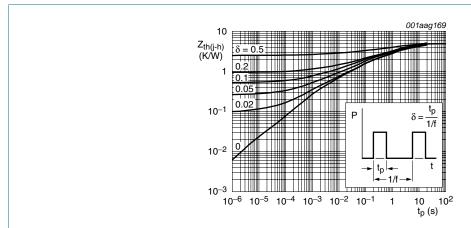


Fig 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

## 6. Isolation characteristics

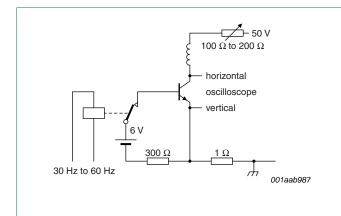
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>h</sub> = 25 °C; from all terminals to external heatsink; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from collector to external heatsink ; f = 1 MHz; $T_h = 25 \ ^{\circ}\text{C}$	-	10	-	pF

# 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
I <sub>CES</sub>	collector-emitter cut-off current	$V_{BE} = 0 \text{ V}; V_{CE} = 1050 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.2	10	μΑ
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{h} = 25 ^{\circ}\text{C}$	-	10	250	μΑ
$V_{(BR)EBO}$	open-collector emitter-base breakdown voltage	$I_B = 1 \text{ mA}; I_C = 0 \text{ A}; T_h = 25 \text{ °C}$	15	19	-	V
$V_{CEOsus}$	collector-emitter sustaining voltage	$I_B = 0 \text{ A}$ ; $I_C = 10 \text{ mA}$ ; $L_C = 25 \text{ mH}$ ; $T_h = 25 \text{ C}$ ; see Figure 6; see Figure 7	400	470	-	V
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 1 \text{ A}$ ; $I_B = 0.2 \text{ A}$ ; $T_h = 25 \text{ °C}$ ; see Figure 8; see Figure 9	-	0.15	0.5	V
		$I_C = 3.5 \text{ A}$ ; $I_B = 1 \text{ A}$ ; $T_h = 25 \text{ °C}$ ; see <u>Figure 8</u> ; see <u>Figure 9</u>	-	0.6	1.5	V
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 3.5 \text{ A}$ ; $I_B = 1 \text{ A}$ ; $T_h = 25 \text{ C}$ ; see Figure 10	-	1.1	1.5	V
h <sub>FE</sub>	DC current gain	$I_C = 0.1 \text{ A}; V_{CE} = 5 \text{ V}; T_h = 25 \text{ C};$ see Figure 11	48	66	100	
		$I_C$ = 0.8 A; $V_{CE}$ = 3 V; $T_h$ = 25 °C; see Figure 12	25	42	50	
Dynamic ch	aracteristics					
ts	storage time	$I_C = 2.5 \text{ A}$ ; $I_{Bon} = 0.5 \text{ A}$ ; $I_{Boff} = -0.5 \text{ A}$ ;	-	-	3.5	μs
t <sub>f</sub>	fall time	$R_L$ = 60 Ω; $V_{BB}$ = -5 V; $T_h$ = 25 °C; resistive load; $t_p$ = 300 μs; see Figure 13; see Figure 14	-	-	500	ns





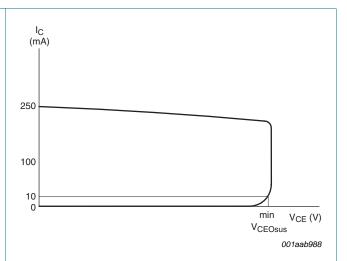


Fig 7. Oscilloscope display for collector-emitter sustaining voltage test waveform

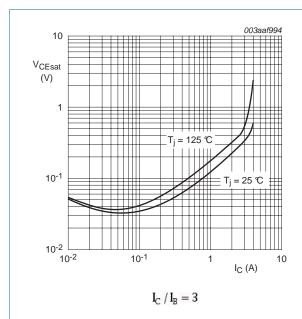


Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

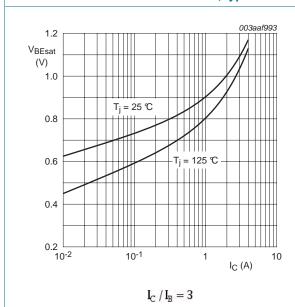


Fig 10. Base-emitter saturation voltage as a function of collector current; typical values

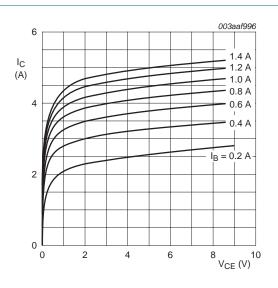


Fig 9. Collector current as a function of collector-emitter voltage; typical values

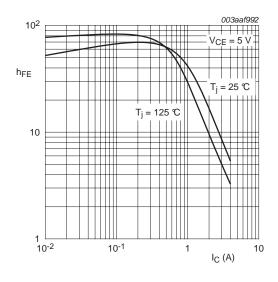


Fig 11. DC current gain as a function of collector current; typical values

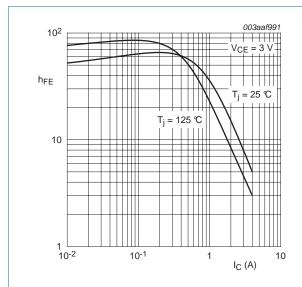
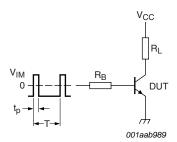


Fig 12. DC current gain as a function of collector current; typical values



 $V_{IM}=-6$  to +8 V;  $V_{CC}=250$  V;  $t_p=20$   $\mu s$ ;  $\boldsymbol{\delta}=\frac{t_p}{T}=0.01$   $R_B$  and  $R_L$  calculated from  $I_{Con}$  and  $I_{Bon}$  requirements.

Fig 13. Test circuit for resistive load switching

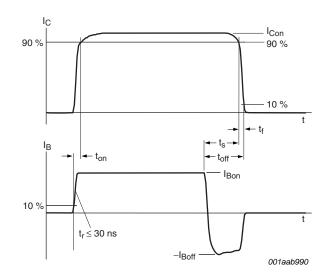
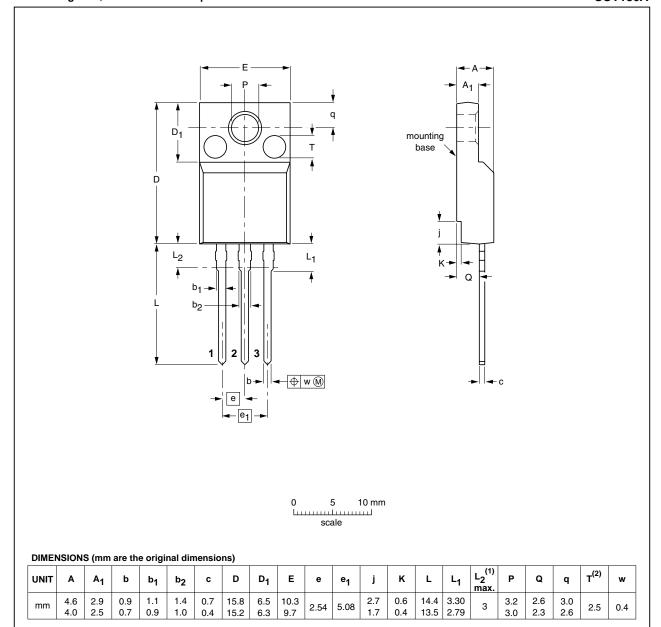


Fig 14. Switching times waveforms for resistive load

# 8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



#### Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are  $\varnothing$  2.5  $\times$  0.8 max. depth

	REFER	ENCES		EUROPEAN	ISSUE DATE
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	3-lead TO-220F				<del>-02-04-09</del> 06-02-14
	IEC	IEC JEDEC	IEC JEDEC JEITA		IEC JEDEC JEITA PROJECTION

Fig 15. Package outline SOT186A (TO-220F)

BUJ302AX

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# 9. Revision history

## Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ302AX v.2	20110328	Product data sheet	-	BUJ302AX v.1
Modifications:	<ul> <li>The format of to of NXP Semice</li> </ul>		lesigned to comply with	the new identity guidelines
	<ul> <li>Legal texts have</li> </ul>	ve been adapted to the new	company name where	appropriate.
BUJ302AX v.1	19980801	Objective specification	١ -	-

# 10. Legal information

#### 10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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